Contents STx11NM60N

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STx11NM60N Electrical ratings

# 1 Electrical ratings

Table 2. Absolute maximum ratings

		Value		
Symbol	Parameter	TO-220,I²PAK, D²PAK,DPAK,IPAK	TO-220FP	Unit
$V_{DS}$	Drain-source voltage (V <sub>GS</sub> = 0)	600		V
V <sub>GS</sub>	Gate-source voltage	± 25		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	10	10 <sup>(1)</sup>	Α
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	6.3	6.3 <sup>(1)</sup>	Α
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	40	40 <sup>(1)</sup>	Α
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	90	25	W
	Derating factor	0.8	0.2	W/°C
dv/dt (3)	Peak diode recovery voltage slope	15		V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; $T_C$ = 25 °C)		2500	V
T <sub>stg</sub>	Storage temperature	-55 to 150	•	°C
TJ	Max. operating junction temperature	150		°C

- 1. Limited only by maximum temperature allowed
- 2. Pulse width limited by safe operating area
- 3.  $I_{SD} \leq$  10 A, di/dt  $\leq$  400 A/ $\mu$ s,  $V_{DD}$  = 80%  $V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value						Unit
Symbol	Parameter	TO-220	I <sup>2</sup> PAK	DPAK	D <sup>2</sup> PAK	IPAK	TO-220FP	Oill
R <sub>thj-case</sub>	Thermal resistance junction-case max			1.38			5	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-amb max	62	.5			100	62.5	°C/W
R <sub>thj-pcb</sub>	Thermal resistance junction-pcb max			50	30			°C/W
T <sub>I</sub>	Maximum lead temperature for soldering purposes			,	300			°C

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I <sub>AS</sub>	Avalanche current, repetitive or not-repetitive (pulse width limited by T <sub>J</sub> max)	3.5	Α
E <sub>AS</sub>	Single pulse avalanche energy (starting $T_J = 25$ °C, $I_D = I_{AS}$ , $V_{DD} = 50$ V)	200	mJ

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Electrical characteristics STx11NM60N

## 2 Electrical characteristics

(T<sub>CASE</sub>=25 °C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0	600			V
dv/dt <sup>(1)</sup>	Drain-source voltage slope	$V_{DD} = 400 \text{ V,I}_{D} = 5 \text{ A,}$ $V_{GS} = 10 \text{ V}$		45		V/ns
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max rating, V <sub>DS</sub> =Max rating,Tc=125 °C			1 10	μ <b>Α</b> μ <b>Α</b>
I <sub>GSS</sub>	Gate body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ±20 V			±100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	3	4	V
R <sub>DS(on)</sub>	Static drain-source on resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A		0.37	0.45	Ω

<sup>1.</sup> Characteristic value at turn off on inductive load

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	$V_{DS} = 15 \text{ V}, I_{D} = 5 \text{ A}$		7.5		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	V <sub>DS</sub> =50 V, f=1 MHz, V <sub>GS</sub> =0		850 44 5		pF pF pF
C <sub>oss eq.</sub> <sup>(2)</sup>	Equivalent output capacitance	V <sub>GS</sub> =0, V <sub>DS</sub> =0 to 480 V		130		pF
Rg	Gate input resistance	f=1 MHz Gate DC Bias=0 Test signal level=20 mV open drain		3.7		Ω
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total gate charge Gate-source charge Gate-drain charge	$V_{DD}$ =480 V, $I_{D}$ = 10 A $V_{GS}$ =10 V Figure 19		31 4.2 15.9		nC nC nC

<sup>1.</sup> Pulsed: pulse duration =  $300\mu s$ , duty cycle 1.5%

<sup>2.</sup>  $C_{oss\ eq.}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ 

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t <sub>d(on)</sub>	Turn-on delay time	$V_{DD} = 300 \text{ V}, I_D = 5 \text{ A},$		22		ns
ì,	Rise time	$R_G = 4.7 \Omega, V_{GS} = 10 V$		18.5		ns
t <sub>d(off)</sub>	Turn-off delay time	Figure 18		50		ns
ì, ′	Fall time	Figure 23		12		ns

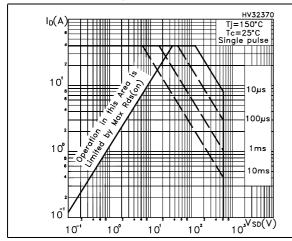
Table 8. Source drain diode

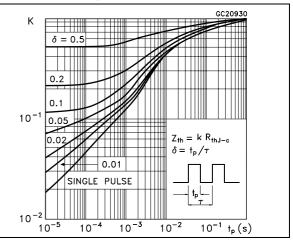
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>SD</sub> I <sub>SDM</sub>	Source-drain current Source-drain current (pulsed)				10 40	A A
V <sub>SD</sub> <sup>(1)</sup>	Forward on voltage	I <sub>SD</sub> = 10 A, V <sub>GS</sub> =0			1.3	V
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}$ =10 A, di/dt =100 A/ $\mu$ s, V <sub>DD</sub> =100 V Figure 20		340 3.26 19.2		ns µC A
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$V_{DD}$ = 100 V di/dt = 100 A/µs, $I_{SD}$ = 10 A $T_{J}$ = 150 °C <i>Figure 20</i>		460 4.42 19.2		ns µC A

<sup>1.</sup> Pulsed: pulse duration = 300µs, duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, Figure 3. Thermal impedance for TO-220, I2PAK, D2PAK





Electrical characteristics STx11NM60N

Figure 4. Safe operating area for TO-220FP Figure 5. Thermal impedance for TO-220FP

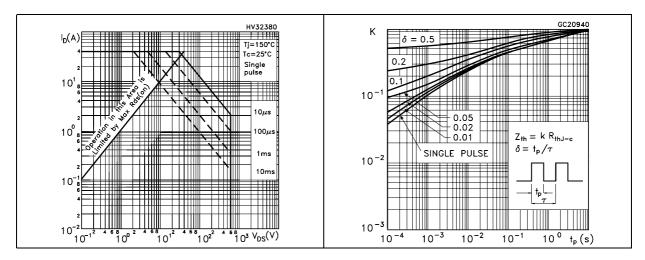


Figure 6. Safe operating area for DPAK, IPAK Figure 7. Thermal impedance for DPAK, IPAK

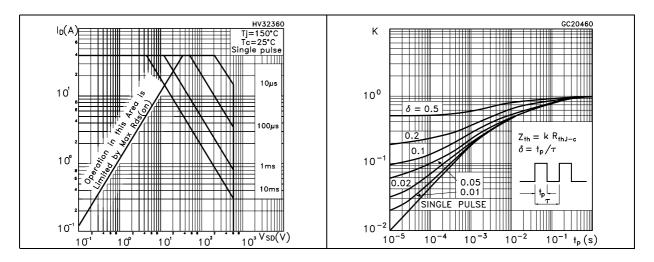
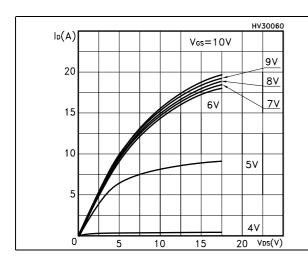


Figure 8. Output characteristics

Figure 9. Transfer characteristics



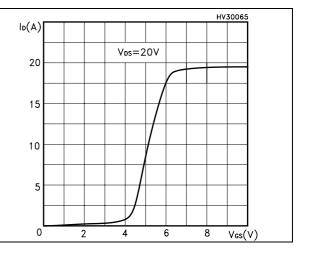
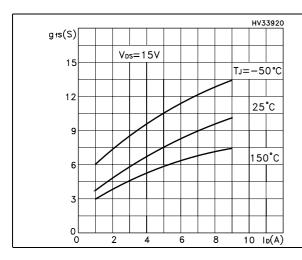


Figure 10. Transconductance

Figure 11. Static drain-source on resistance



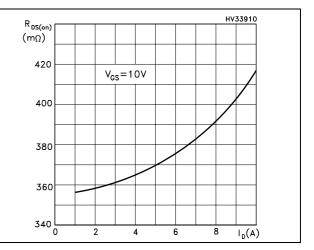
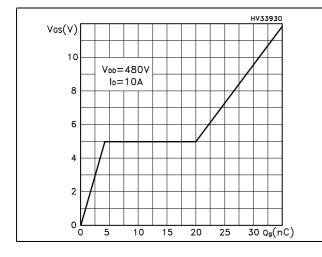
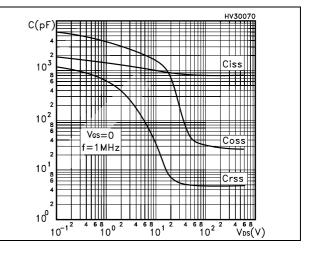


Figure 12. Gate charge vs gate-source voltage Figure 13. Capacitance variations

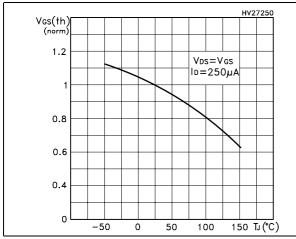




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Electrical characteristics STx11NM60N

Figure 14. Normalized gate threshold voltage Figure 15. Normalized on resistance vs vs temperature temperature



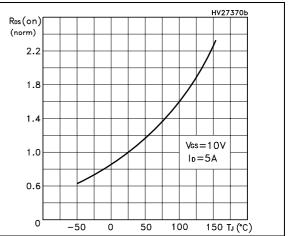
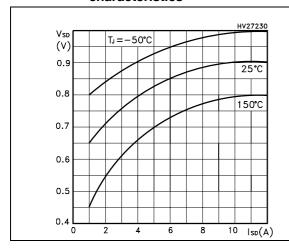
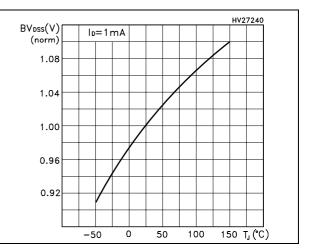


Figure 16. Source-drain diode forward characteristics

Figure 17. Normalized  $B_{VDSS}$  vs temperature





STx11NM60N Test circuits

## 3 Test circuits

Figure 18. Switching times test circuit for resistive load

Figure 19. Gate charge test circuit

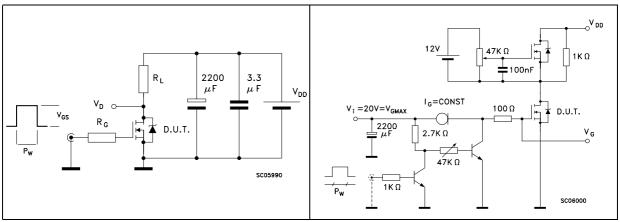


Figure 20. Test circuit for inductive load switching and diode recovery times

Figure 21. Unclamped inductive load test circuit

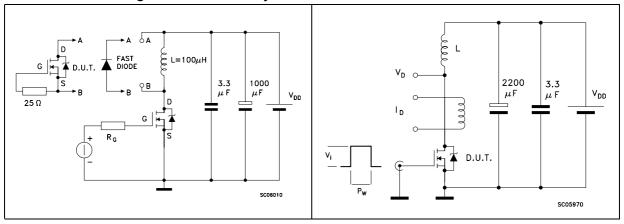
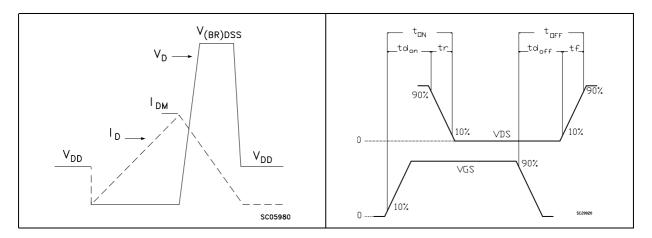


Figure 22. Unclamped inductive waveform

Figure 23. Switching time waveform



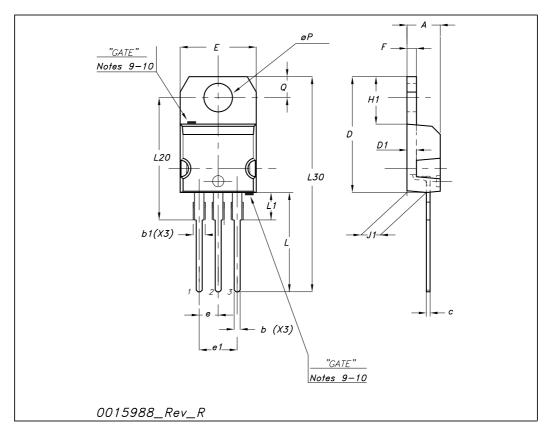
# 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

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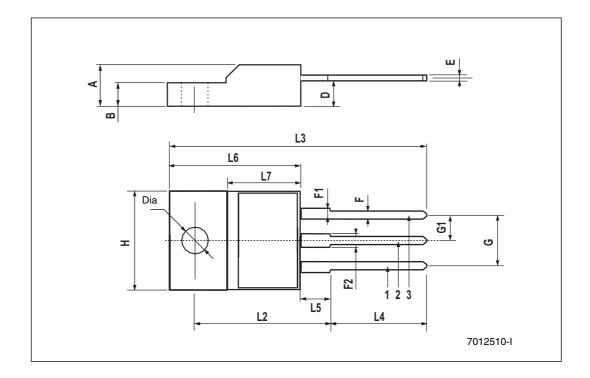
#### TO-220 mechanical data

Dim		mm			inch	
Dim	Min	Тур	Max	Min	Тур	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90	İ		1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65	İ	2.95	0.104		0.116



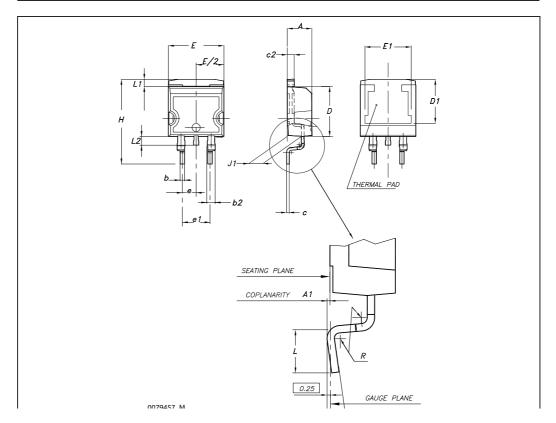
<b>TO-220FP</b>	mechan	ical data
I U-ZZUFF	IIIeciiaii	icai uata

Dim.		mm.			inch	
Dim.	Min.	Тур	Max.	Min.	Тур.	Max.
A	4.40		4.60	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.70	0.017		0.027
F	0.75		1.00	0.030		0.039
F1	1.15		1.50	0.045		0.067
F2	1.15		1.50	0.045		0.067
G	4.95		5.20	0.195		0.204
G1	2.40		2.70	0.094		0.106
Н	10		10.40	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.80		10.60	0.385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.90		16.40	0.626		0.645
L7	9		9.30	0.354		0.366
Dia	3		3.2	0.118		0.126



### D<sup>2</sup>PAK (TO-263) mechanical data

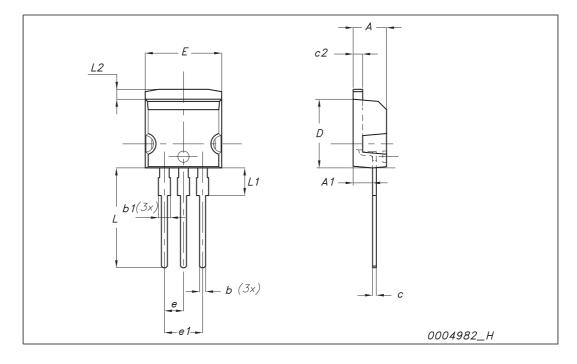
Dim		mm			inch	
Dim	Min	Тур	Max	Min	Тур	Max
Α	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
С	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
Е	10		10.40	0.394		0.409
E1	8.50			0.334		
е		2.54			0.1	
e1	4.88		5.28	0.192		0.208
Н	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°	İ	8°	0°		8°



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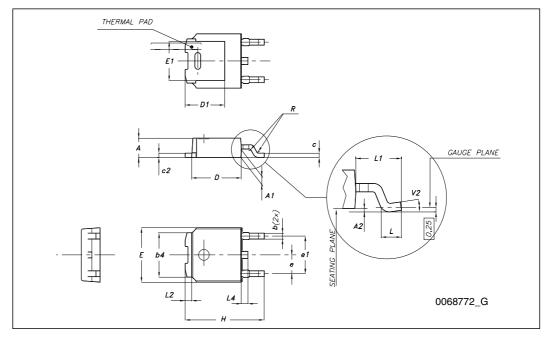
### I<sup>2</sup>PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Тур	Max	Min	Тур	Max
А	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



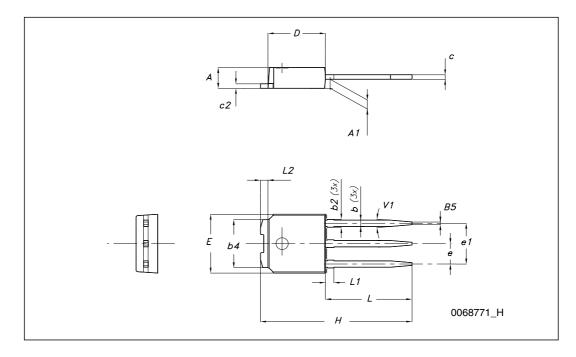
### TO-252 (DPAK) mechanical data

DIM.	mm.			
	min.	typ	max.	
Α	2.20		2.40	
A1	0.90		1.10	
A2	0.03		0.23	
b	0.64		0.90	
b4	5.20		5.40	
С	0.45		0.60	
c2	0.48		0.60	
D	6.00		6.20	
D1		5.10		
E	6.40		6.60	
E1		4.70		
е		2.28		
e1	4.40		4.60	
Н	9.35		10.10	
L	1			
L1		2.80		
L2		0.80		
L4	0.60		1	
R		0.20		
V2	0 °		8°	



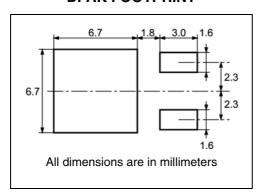
TO-251 (IPAK) n	nechanical data
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DIM.	mm.			
	min.	typ	max.	
Α	2.20		2.40	
A1	0.90		1.10	
b	0.64		0.90	
b2			0.95	
b4	5.20		5.40	
С	0.45		0.60	
c2	0.48		0.60	
D	6.00		6.20	
E	6.40		6.60	
е		2.28		
e1	4.40		4.60	
Н		16.10		
L	9.00		9.40	
(L1)	0.80		1.20	
L2		0.80		
V1		10 °		

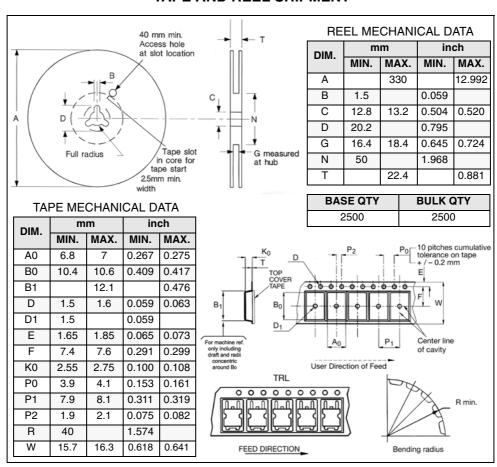


## 5 Packaging mechanical data

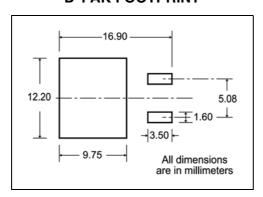
#### **DPAK FOOTPRINT**



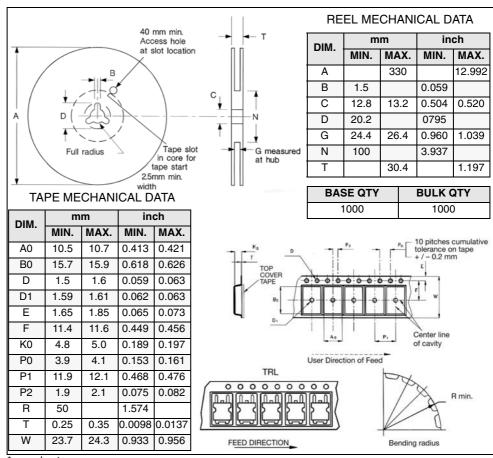
#### **TAPE AND REEL SHIPMENT**



### **D<sup>2</sup>PAK FOOTPRINT**



#### **TAPE AND REEL SHIPMENT**



<sup>\*</sup> on sales type

STx11NM60N Revision history

# 6 Revision history

Table 9. Document revision history

Date	Revision	Changes
03-Aug-2006	1	First release
14-Nov-2006	2	Complete version
02-Oct-2007	3	Figure 8.: Output characteristics has been updated. Added new package (IPPAK)
03-Mar-2008	4	Added new package D²PAK
03-Mar-2009	5	Figure 2, Figure 4 and Figure 6 corrected.

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